AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): A semiconductor device module structure comprising:

a high-resistance layer of a first conductive type;

a base layer of a second conductive type formed in an upper part of the high-resistance layer of the first conductive type;

an emitter region of a first conductive type formed in an upper part of the base layer of the second conductive type;

an emitter electrode connected to the emitter region;

an insulated gate electrode adjacent to the base layer of the second conductive type;

a guard ring part ~~where diffusion~~, wherein a portion of the guard ring has been made deep around a cell region including the emitter region ~~has been made deep~~;

a passivation layer formed on ~~the~~ an upper part of the guard ring part and not extending onto ~~the~~an upper part of the cell region;

a buffer layer of a first conductive type formed on an underside of the high-resistance layer of the first conductive type;

a collector layer of the second conductive type formed on ~~the~~ an underside of ~~a~~ the buffer layer of the first conductive type;

a collector electrode connected to the collector layer; and

a metal flat plate upper heat-sinking part connected to the emitter electrode at a height such that it is non-contacting with the passivation film.

Claim 2 (currently amended): The semiconductor device module structure of claim 1, ~~characterized in that the module structure of a~~wherein the semiconductor device module structure ~~further~~ comprises a diode part, and wherein a cathode electrode ~~at~~located in an upper part of the diode part between the high-resistance layer and the upper heat-sinking part ~~are~~is connected to the upper heat-sinking part.

Claim 3 (new): The semiconductor device module structure of claim 1, wherein one end of the metal flat plate upper heat-sinking part is connected to the emitter electrode and the opposite end of the metal flat plate heat-sinking part is connected to a substrate.